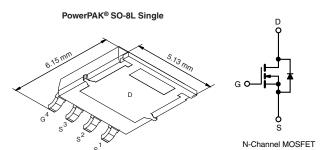


www.vishay.com

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY | |
|---|--------|
| V _{DS} (V) | 40 |
| $R_{DS(on)}$ (Ω) at $V_{GS} = 10 \text{ V}$ | 0.0045 |
| $R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$ | 0.0055 |
| I _D (A) | 60 |
| Configuration | Single |



FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^o
- 100 % Rq and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

| ORDERING INFORMATION | |
|---------------------------------|-----------------|
| Package | PowerPAK SO-8L |
| Lead (Pb)-free and Halogen-free | SQJ886EP-T1-GE3 |

| PARAMETER | SYMBOL | LIMIT | UNIT | | | |
|--|-------------------------|-----------------------------------|---------------|----|--|--|
| Drain-Source Voltage | | V _{DS} | 40 | | | |
| Gate-Source Voltage | | V _{GS} | ± 20 | V | | |
| Continuous Dusin Comment | T _C = 25 °C | 1 | 60 | А | | |
| Continuous Drain Current | T _C = 125 °C | I _D | 45 | | | |
| Continuous Source Current (Diode Conduction) | | I _S | 50 | | | |
| Pulsed Drain Current ^a | | I _{DM} | 240 | | | |
| Single Pulse Avalanche Current | J 0.1 mal J | I _{AS} | 36 | | | |
| Single Pulse Avalanche Energy | L = 0.1 mH | E _{AS} | 64 | mJ | | |
| Maximum Power Dissipation ^a | T _C = 25 °C | D | 55 | W | | |
| | T _C = 125 °C | P_{D} | 18 | VV | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to + 175 | °C | | |
| Soldering Recommendations (Peak Temperature) ^{d, e} | | | 260 | | | |

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------|------------------------|------------|-------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Junction-to-Ambient | PCB Mount ^b | R_{thJA} | 70 | °C/W |
| Junction-to-Case (Drain) | | R_{thJC} | 2.7 | C/VV |

Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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| PARAMETER | SYMBOL | TES | T CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
|---|--------------------------|--|--|------|--------|--------|------|--|
| Static | 1 | | | ı | | ı | ı | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0$, $I_D = 250 \mu A$ | | 40 | - | - | V | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = | = V _{GS} , I _D = 250 μA | 1.5 | 2.0 | 2.5 | V | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = | 0 V, V _{GS} = ± 20 V | - | - | ± 100 | nA | |
| | | V _{GS} = 0 V | V _{DS} = 40 V | - | - | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V | V _{DS} = 40 V, T _J = 125 °C | - | - | 50 | μΑ | |
| | | V _{GS} = 0 V | V _{DS} = 40 V, T _J = 175 °C | - | - | 250 | | |
| On-State Drain Current ^a | I _{D(on)} | V _{GS} = 10 V | V _{DS} ≥ 5 V | 30 | - | - | Α | |
| | | V _{GS} = 10 V | I _D = 15.3 A | - | 0.0036 | 0.0045 | Ω | |
| Dunin Course On Chata Basistanas | | V _{GS} = 4.5 V | I _D = 13.8 A | - | 0.0045 | 0.0055 | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 10 V | I _D = 15.3 A, T _J = 125 °C | - | - | 0.0072 | | |
| | | V _{GS} = 10 V | I _D = 15.3 A, T _J = 175 °C | - | - | 0.0088 | | |
| Forward Transconductanceb | 9 _{fs} | V _{DS} = 15 V, I _D = 15.3 A | | - | 105 | - | S | |
| Dynamic ^b | | | | | | | | |
| Input Capacitance | C _{iss} | | | - | 2338 | 2922 | pF | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 V$ | V _{DS} = 20 V, f = 1 MHz | - | 356 | 445 | | |
| Reverse Transfer Capacitance | C _{rss} | 1 | | - | 147 | 184 | | |
| Total Gate Charge ^c | Qg | | | - | 43 | 65 | | |
| Gate-Source Charge ^c | Q _{gs} | V _{GS} = 10 V | $V_{DS} = 20 \text{ V}, I_{D} = 20 \text{ A}$ | - | 8 | - | nC | |
| Gate-Drain Charge ^c | Q _{gd} | 1 | | - | 7 | - | | |
| Gate Resistance | R_{g} | f = 1 MHz | | 1.25 | 2.45 | 5 | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | | | 8 | 12 | | |
| Rise Time ^c | t _r | $V_{DD} = 20 \text{ V}, \text{ R}_L = 2 \Omega$ $I_D \cong 10 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$ | | - | 17 | 25 | ns | |
| Turn-Off Delay Time ^c | t _{d(off)} | | | - | 29 | 44 | | |
| Fall Time ^c | t _f | | | - | 6 | 9 | 1 | |
| Source-Drain Diode Ratings and Chara | acteristics ^b | | | | • | | | |
| Pulsed Current ^a | I _{SM} | | | - | - | 240 | Α | |
| Forward Voltage | V _{SD} | I _E = 10.1 A, V _{GS} = 0 - 0.8 1.2 | | 1.2 | V | | | |

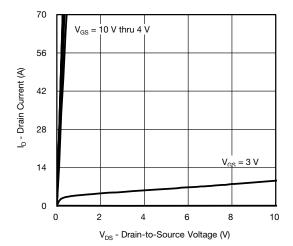
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

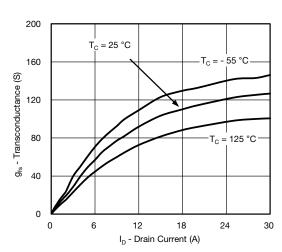
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



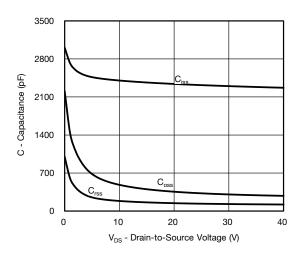
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



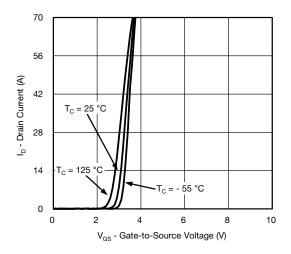
Output Characteristics



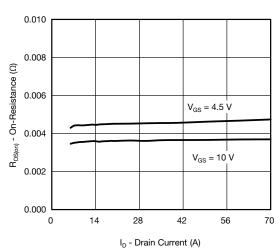
Transconductance



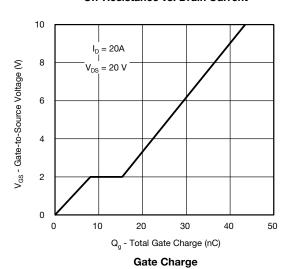
Capacitance



Transfer Characteristics

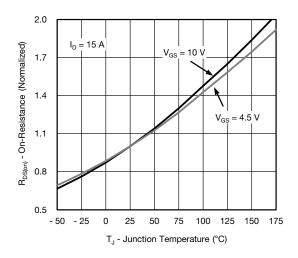


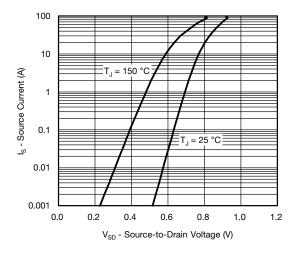
On-Resistance vs. Drain Current



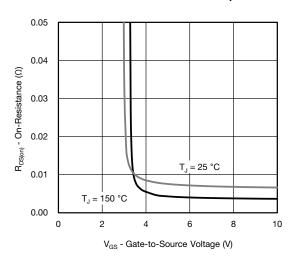


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

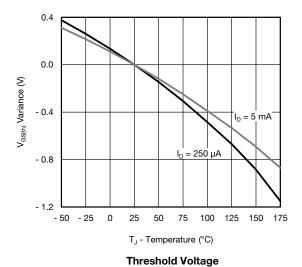




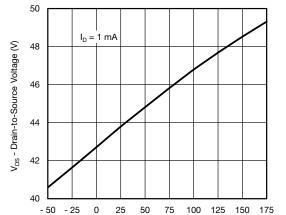
On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

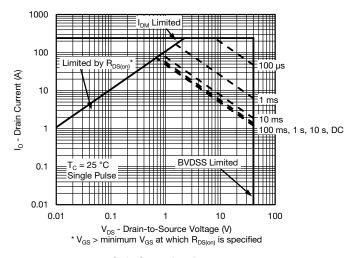


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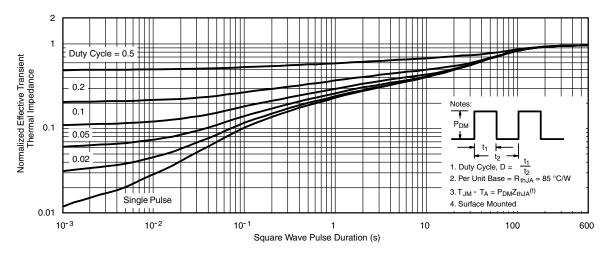
 $\label{eq:TJ} \textbf{T}_{J} \text{ - Junction Temperature (°C)}$ Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



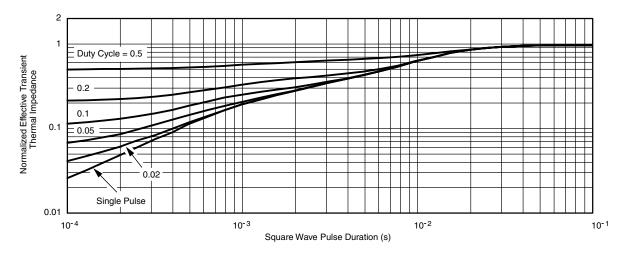
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg262790.

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PowerPAK® SO-8L

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK SO-8L package:

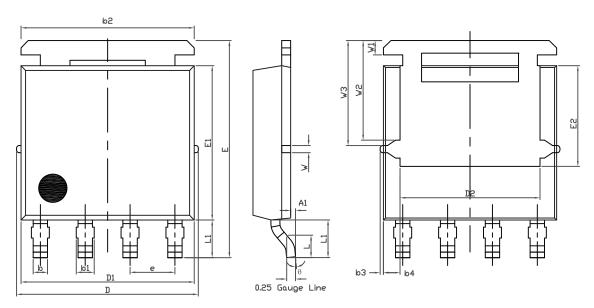
| DATASHEET PART NUMBER | OLD ORDERING CODE a | NEW ORDERING CODE |
|-----------------------|---------------------|-------------------|
| SQJ200EP | - | SQJ200EP-T1_GE3 |
| SQJ401EP | SQJ401EP-T1-GE3 | SQJ401EP-T1_GE3 |
| SQJ402EP | SQJ402EP-T1-GE3 | SQJ402EP-T1_GE3 |
| SQJ403EEP | SQJ403EEP-T1-GE3 | SQJ403EEP-T1_GE3 |
| SQJ403EP | - | SQJ403EP-T1_GE3 |
| SQJ410EP | SQJ410EP-T1-GE3 | SQJ410EP-T1_GE3 |
| SQJ412EP | SQJ412EP-T1-GE3 | SQJ412EP-T1_GE3 |
| SQJ422EP | SQJ422EP-T1-GE3 | SQJ422EP-T1_GE3 |
| SQJ431EP | SQJ431EP-T1-GE3 | SQJ431EP-T1_GE3 |
| SQJ443EP | SQJ443EP-T1-GE3 | SQJ443EP-T1_GE3 |
| SQJ456EP | SQJ456EP-T1-GE3 | SQJ456EP-T1_GE3 |
| SQJ460AEP | - | SQJ460AEP-T1_GE3 |
| SQJ461EP | SQJ461EP-T1-GE3 | SQJ461EP-T1_GE3 |
| SQJ463EP | SQJ463EP-T1-GE3 | SQJ463EP-T1_GE3 |
| SQJ465EP | SQJ465EP-T1-GE3 | SQJ465EP-T1_GE3 |
| SQJ469EP | SQJ469EP-T1-GE3 | SQJ469EP-T1_GE3 |
| SQJ486EP | SQJ486EP-T1-GE3 | SQJ486EP-T1_GE3 |
| SQJ488EP | SQJ488EP-T1-GE3 | SQJ488EP-T1_GE3 |
| SQJ500AEP | SQJ500AEP-T1-GE3 | SQJ500AEP-T1_GE3 |
| SQJ840EP | SQJ840EP-T1-GE3 | SQJ840EP-T1_GE3 |
| SQJ844AEP | SQJ844AEP-T1-GE3 | SQJ844AEP-T1_GE3 |
| SQJ850EP | SQJ850EP-T1-GE3 | SQJ850EP-T1_GE3 |
| SQJ858AEP | SQJ858AEP-T1-GE3 | SQJ858AEP-T1_GE3 |
| SQJ886EP | SQJ886EP-T1-GE3 | SQJ886EP-T1_GE3 |
| SQJ910AEP | SQJ910AEP-T1-GE3 | SQJ910AEP-T1_GE3 |
| SQJ912AEP | SQJ912AEP-T1-GE3 | SQJ912AEP-T1_GE3 |
| SQJ940EP | SQJ940EP-T1-GE3 | SQJ940EP-T1_GE3 |
| SQJ942EP | SQJ942EP-T1-GE3 | SQJ942EP-T1_GE3 |
| SQJ951EP | SQJ951EP-T1-GE3 | SQJ951EP-T1_GE3 |
| SQJ952EP | - | SQJ952EP-T1_GE3 |
| SQJ960EP | SQJ960EP-T1-GE3 | SQJ960EP-T1_GE3 |
| SQJ963EP | SQJ963EP-T1-GE3 | SQJ963EP-T1_GE3 |
| SQJ968EP | SQJ968EP-T1-GE3 | SQJ968EP-T1_GE3 |
| SQJ980AEP | SQJ980AEP-T1-GE3 | SQJ980AEP-T1_GE3 |
| SQJ992EP | SQJ992EP-T1-GE3 | SQJ992EP-T1_GE3 |

Note

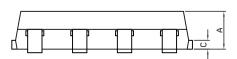
a. Old ordering code is obsolete and no longer valid for new orders

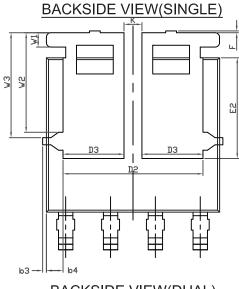
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PowerPAK® SO-8L Case Outline for all Parts



TOPSIDE VIEW





BACKSIDE VIEW(DUAL)



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| DIM. | MILLIMETERS | | | INCHES | | |
|------|-------------|--------------------|-------|--------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX |
| Α | 1.00 | 1.07 | 1.14 | 0.039 | 0.042 | 0.045 |
| A1 | 0.00 | - | 0.127 | 0.00 | - | 0.005 |
| b | 0.33 | 0.41 | 0.48 | 0.013 | 0.016 | 0.019 |
| b1 | 0.44 | 0.51 | 0.58 | 0.017 | 0.020 | 0.023 |
| b2 | 4.80 | 4.90 | 5.00 | 0.189 | 0.193 | 0.197 |
| b3 | | 0.094 | | | 0.004 | |
| b4 | | 0.47 | | | 0.019 | |
| С | 0.20 | 0.25 | 0.30 | 0.008 | 0.010 | 0.012 |
| D | 5.00 | 5.13 | 5.25 | 0.197 | 0.202 | 0.207 |
| D1 | 4.80 | 4.90 | 5.00 | 0.189 | 0.193 | 0.197 |
| D2 | 3.86 | 3.96 | 4.06 | 0.152 | 0.156 | 0.160 |
| D3 | 1.63 | 1.73 | 1.83 | 0.064 | 0.068 | 0.072 |
| е | | 1.27 BSC 0.050 BSC | | | | |
| Е | 6.05 | 6.15 | 6.25 | 0.238 | 0.242 | 0.246 |
| E1 | 4.27 | 4.37 | 4.47 | 0.168 | 0.172 | 0.176 |
| E2 | 2.75 | 2.85 | 2.95 | 0.108 | 0.112 | 0.116 |
| F | - | - | 0.15 | - | - | 0.006 |
| L | 0.62 | 0.72 | 0.82 | 0.024 | 0.028 | 0.032 |
| L1 | 0.92 | 1.07 | 1.22 | 0.036 | 0.042 | 0.048 |
| K | | 0.51 | | | 0.020 | |
| W | 0.23 | | | | 0.009 | |
| W1 | | 0.41 | | | 0.016 | |
| W2 | 2.82 | | | 0.111 | | |
| W3 | | 2.96 | | | 0.117 | |
| q | 0° | - | 10° | 0° | - | 10° |

ECN: C15-1203-Rev. A, 07-Sep-15

DWG: 6044

Note

· Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000